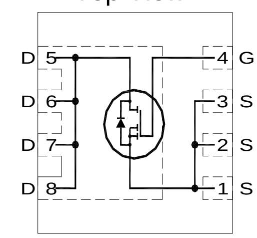
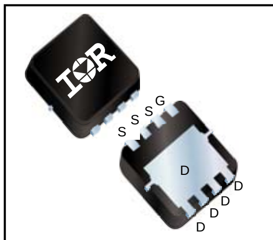
HEXFET® Power MOSFET

V_{DSS}	30	V
V_{GS} max	±20	V
$R_{DS(on)}$ max (@ V_{GS} = 10V)	4.7	mΩ
(@ V_{GS} = 4.5V)	6.7	
Qg (typical)	20	nC
I_D (@$T_{C\,(Bottom)}$ = 25°C)	70⑥	A

Top View





PQFN 3.3X3.3 mm

Applications

- Charge and Discharge Switch for Notebook PC Battery Application
- System/Load Switch
- Synchronous MOSFET for Buck Converters

Features		Benefits
Low Thermal Resistance to PCB (<3.4°C/W)		Enable better thermal dissipation
Low Profile (<1.05 mm)		Increased Power Density
Industry-Standard Pinout	results in	Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques	⇒	Easier Manufacturing
RoHS Compliant Containing no Lead, no Bromide and no Halogen		Environmentally Friendlier
MSL1, Consumer Qualification		Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFHM8326PbF	PQFN 3.3 mm x 3.3 mm	Tape and Reel	4000	IRFHM8326TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	19	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	15	
I_D @ $T_{C(Bottom)}$ = 25°C	Continuous Drain Current, V_{GS} @ 10V	70⑥	
I_D @ $T_{C(Bottom)}$ = 100°C	Continuous Drain Current, V_{GS} @ 10V	44⑥	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Source Bonding Technology Limited)	25⑦	
I_{DM}	Pulsed Drain Current ①	278	
P_D @T_A = 25°C	Power Dissipation ⑤	2.8	W
P_D @$T_{C(Bottom)}$ = 25°C	Power Dissipation ⑤	37	
	Linear Derating Factor ⑤	0.023	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑦ are on page 8

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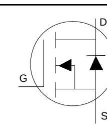
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	22	——	mV/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	3.8	4.7	mΩ	V_{GS} = 10V, I_D = 20A ③
		——	5.2	6.7		V_{GS} = 4.5V, I_D = 20A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.2	1.7	2.2	V	V_{DS} = V_{GS}, I_D = 50µA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	——	-10	——	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	µA	V_{DS} = 24V, V_{GS} = 0V
		——	——	150		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
gfs	Forward Transconductance	70	——	——	S	V_{DS} = 10V, I_D = 20A
Q_g	Total Gate Charge	——	39	——	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 20A
Q_g	Total Gate Charge	——	20	30	nC	V_{DS} = 15V
Q_{gs1}	Pre-Vth Gate-to-Source Charge	——	4.8	——		V_{GS} = 4.5V
Q_{gs2}	Post-Vth Gate-to-Source Charge	——	2.6	——		I_D = 20A
Q_{gd}	Gate-to-Drain Charge	——	6.5	——		
Q_{godr}	Gate Charge Overdrive	——	6.1	——		
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	——	9.1	——		
Q_{oss}	Output Charge	——	11	——	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	——	1.9	——	Ω	
$t_{d(on)}$	Turn-On Delay Time	——	12	——	ns	V_{DD} = 15V, V_{GS} = 4.5V
t_r	Rise Time	——	35	——		I_D = 20A
$t_{d(off)}$	Turn-Off Delay Time	——	18	——		R_G=1.8Ω
t_f	Fall Time	——	12	——		
C_{iss}	Input Capacitance	——	2496	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	524	——		V_{DS} = 10V
C_{rss}	Reverse Transfer Capacitance	——	273	——		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.
E_{AS}	Single Pulse Avalanche Energy ②	——	58
I_{AR}	Avalanche Current ①	——	20

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	25⑦	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	278		
V_{SD}	Diode Forward Voltage	——	——	1.0	V	T_J = 25°C, I_S = 20A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	——	15	23	ns	T_J = 25°C, I_F = 20A, V_{DD} = 15V
Q_{rr}	Reverse Recovery Charge	——	14	21	nC	di/dt = 300A/µs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ④	——	3.4	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ④	——	41	
$R_{\theta JA}$	Junction-to-Ambient ⑤	——	44	
$R_{\theta JA}$ (<10s)	Junction-to-Ambient ⑤	——	31	

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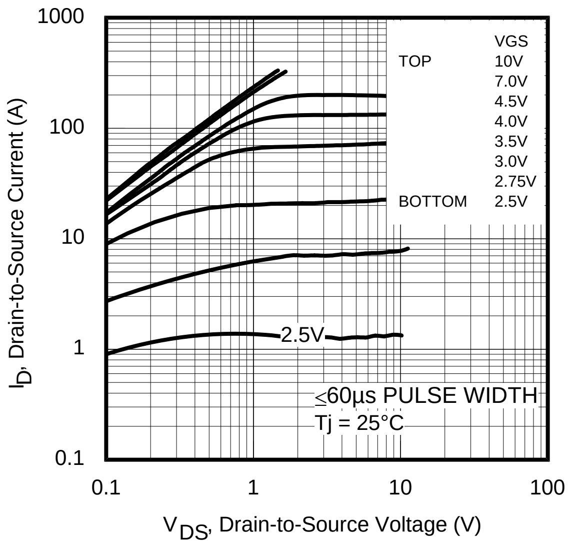

Fig 1. Typical Output Characteristics

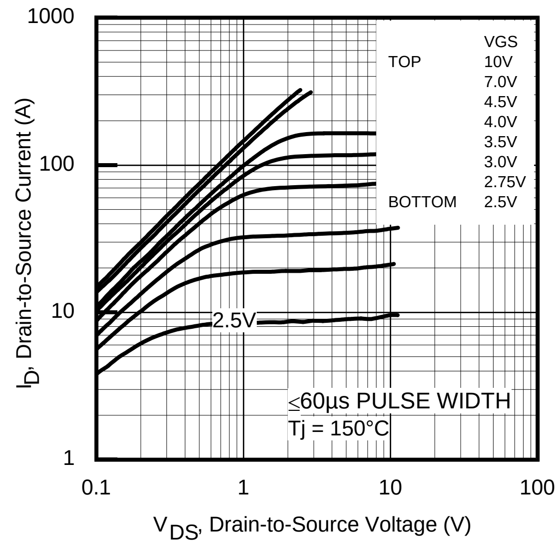

Fig 2. Typical Output Characteristics

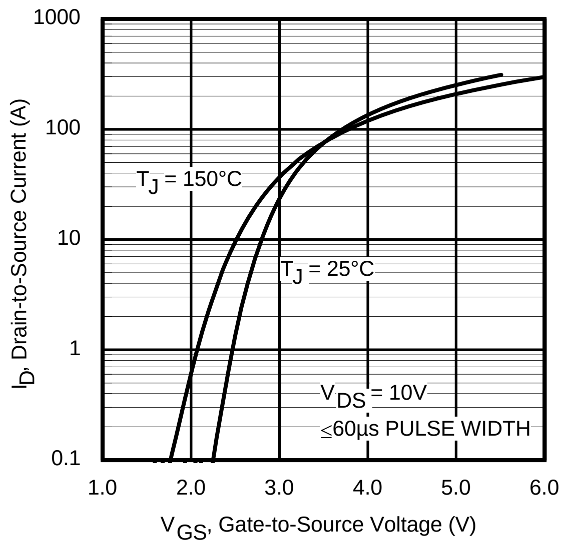

Fig 3. Typical Transfer Characteristics

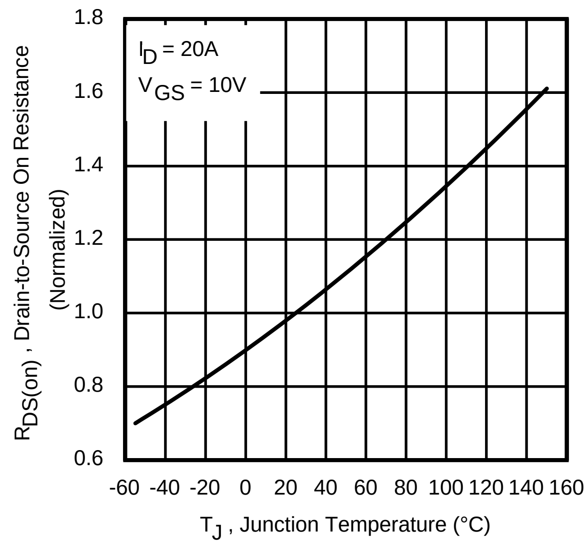

Fig 4. Normalized On-Resistance vs. Temperature

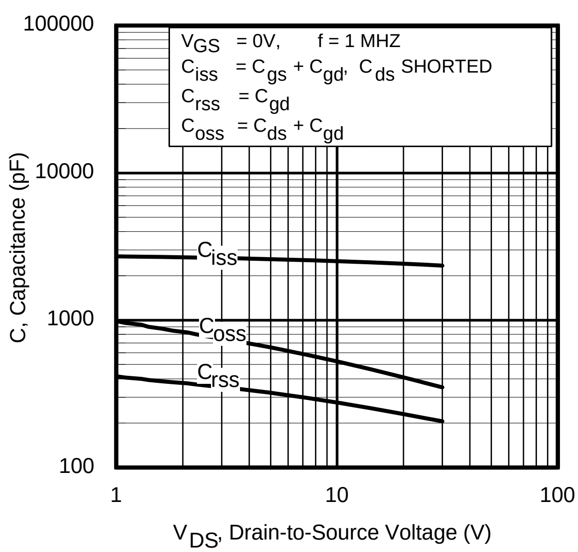

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

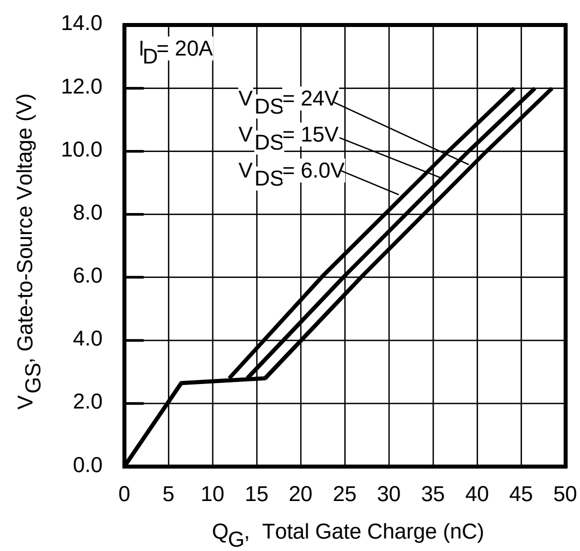

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

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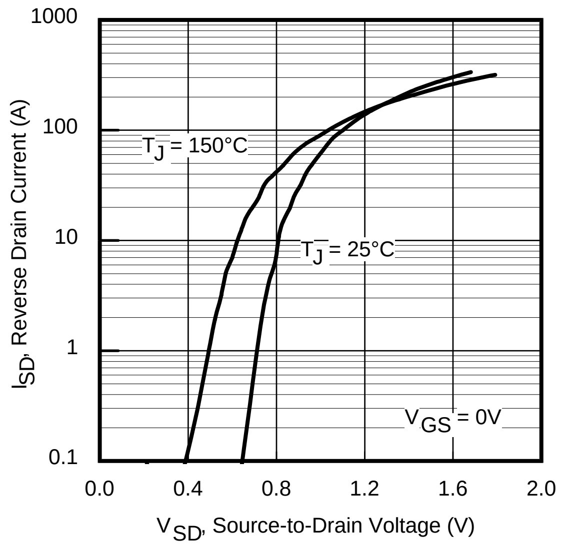

Fig 7. Typical Source-Drain Diode Forward Voltage

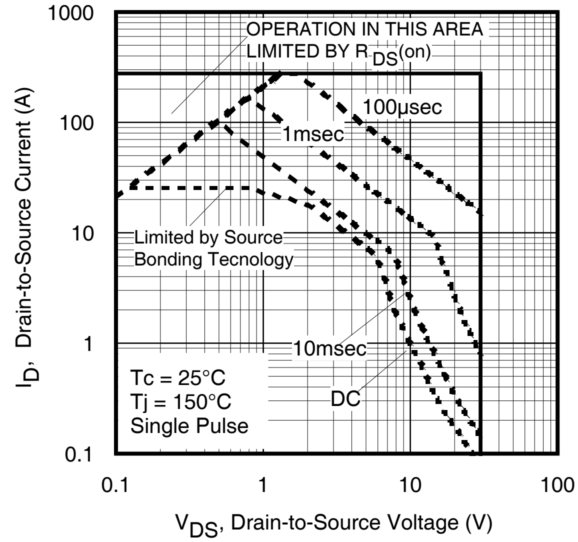

Fig 8. Maximum Safe Operating Area

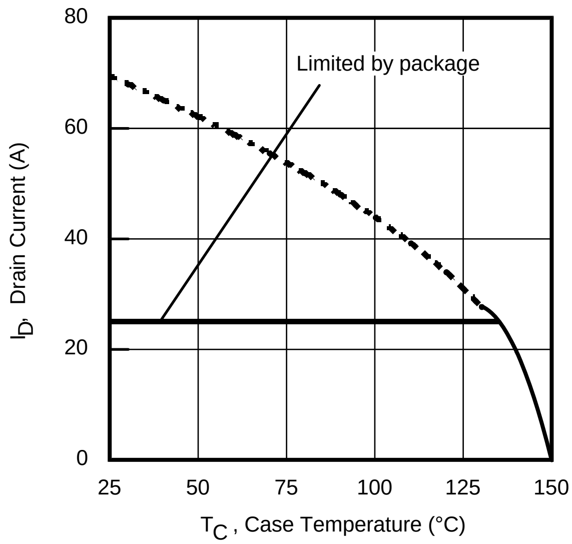

Fig 9. Maximum Drain Current vs. Case Temperature

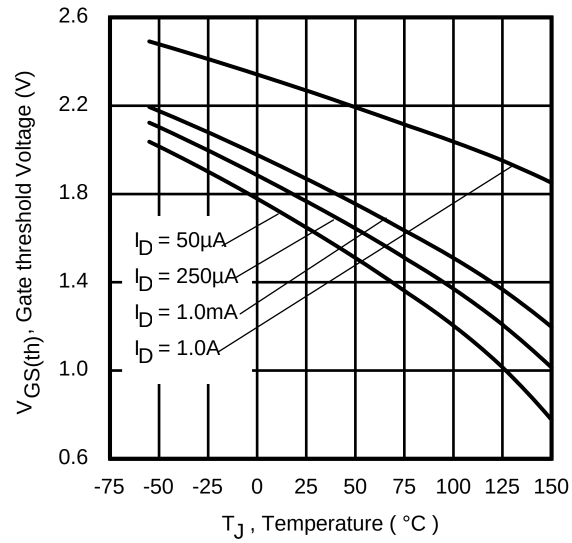

Fig 10. Drain-to–Source Breakdown Voltage

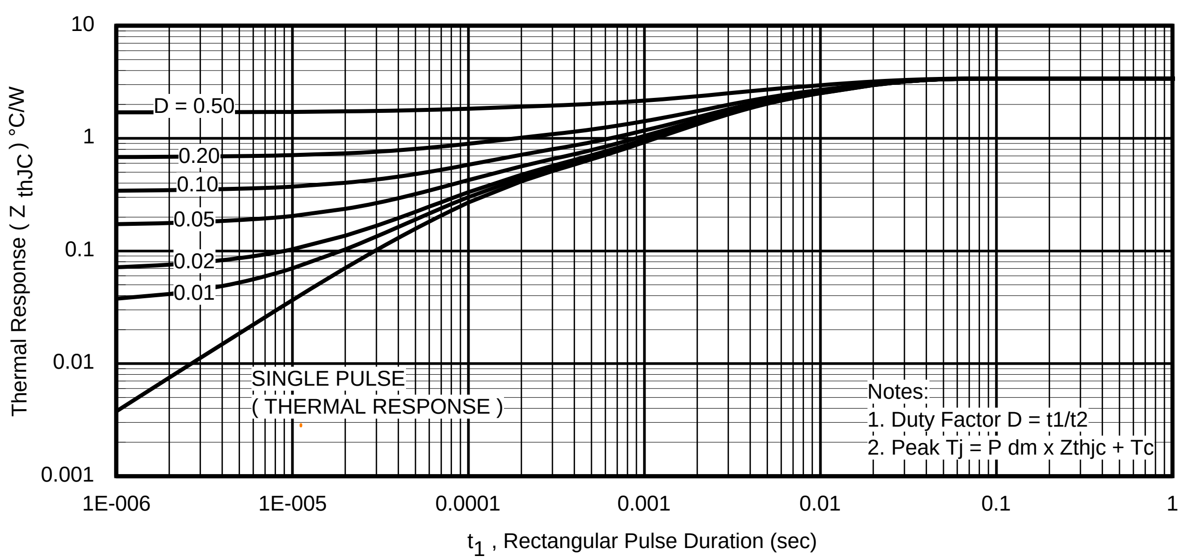

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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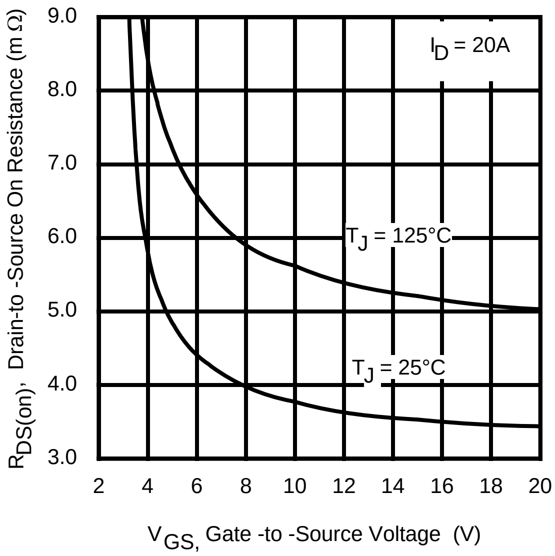

Fig 12. On– Resistance vs. Gate Voltage

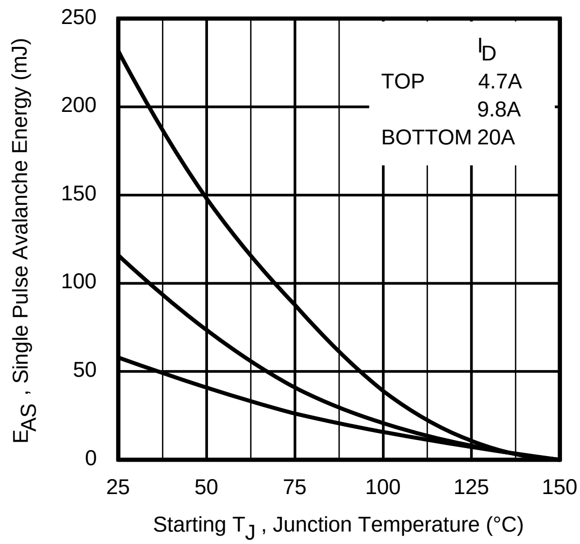

Fig 13. Maximum Avalanche Energy vs. Drain Current

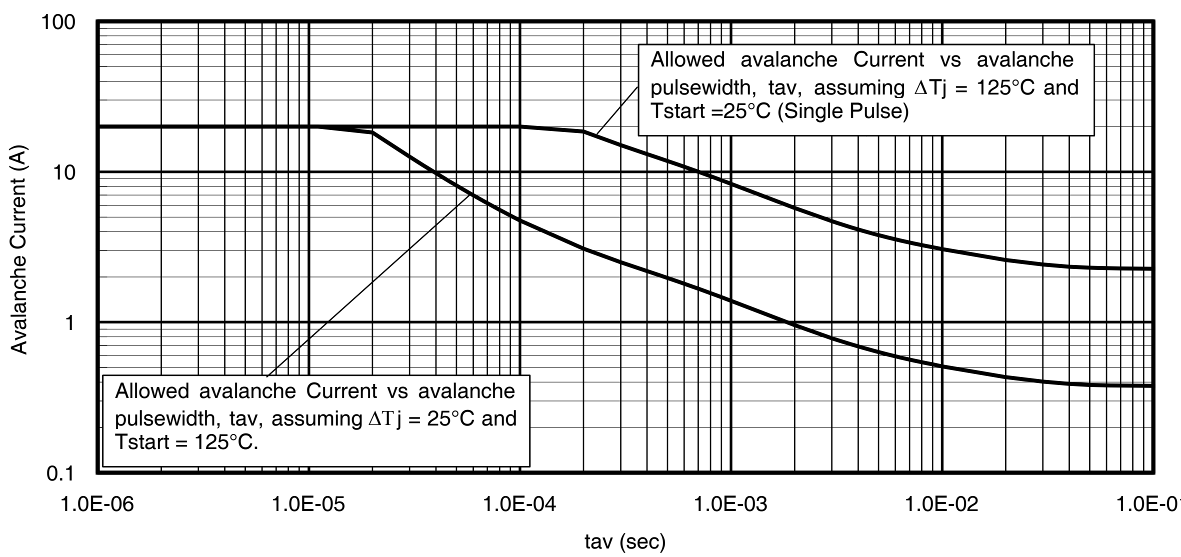

Fig 14. Typical Avalanche Current vs. Pulsewidth

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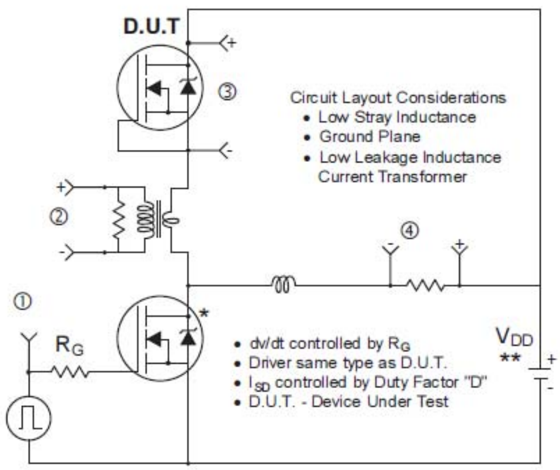

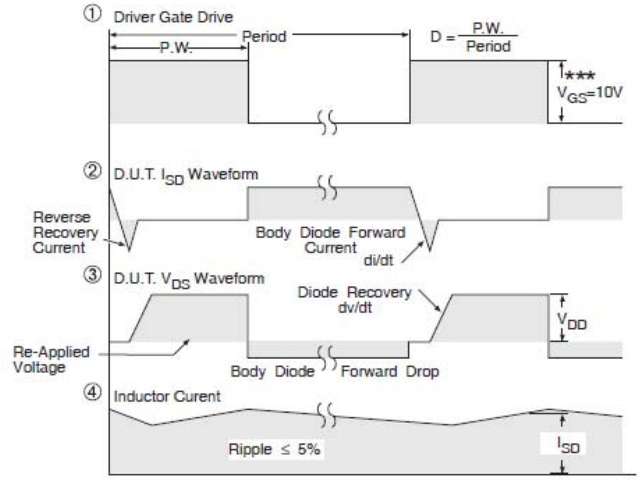

* Use P-Channel Driver for P-Channel Measurements
** Reverse Polarity for P-Channel

*** V_{GS} = 5V for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

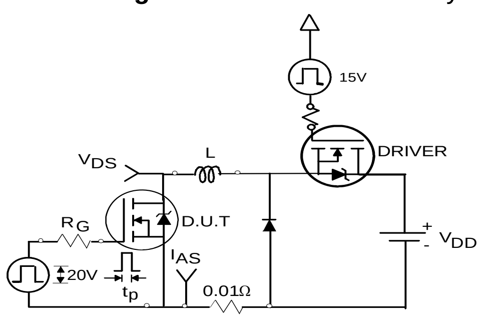

Fig 16a. Unclamped Inductive Test Circuit

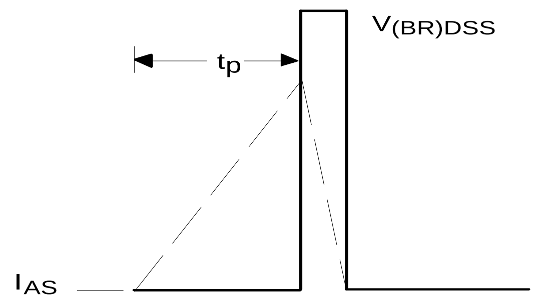

Fig 16b. Unclamped Inductive Waveforms

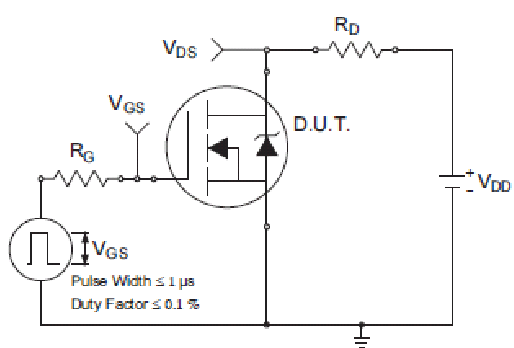

Fig 17a. Switching Time Test Circuit

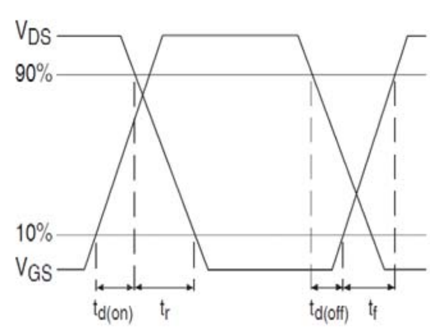

Fig 17b. Switching Time Waveforms

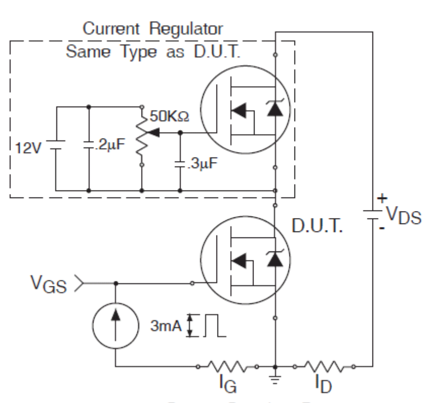

Fig 18a. Gate Charge Test Circuit

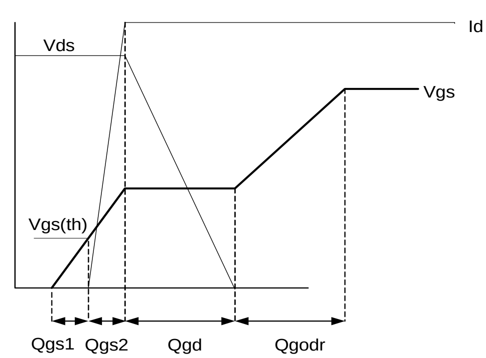

Fig 18b. Gate Charge Waveform

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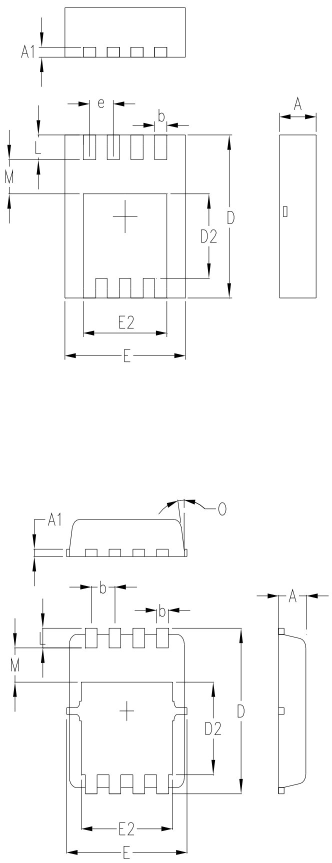
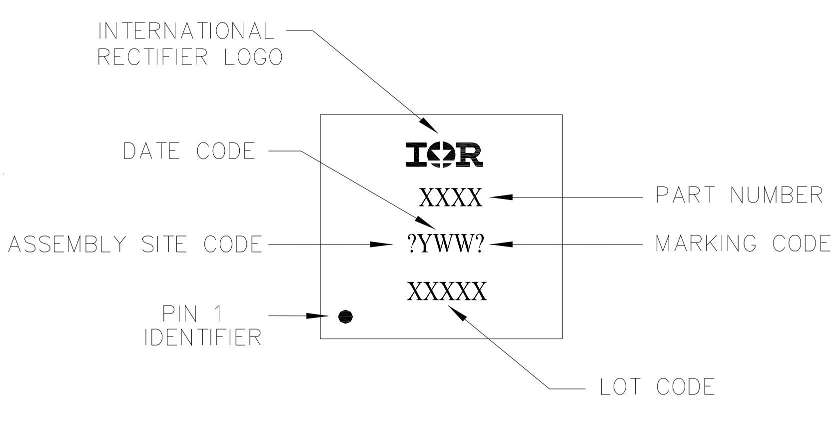
PQFN 3.3mm x 3.3mm Outline Package Details



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.05	0.0276	0.0413
A1	0.25	0.39	0.0098	0.0154
b	0.25	0.39	0.0098	0.0154
D	3.20	3.45	0.1260	0.1358
D2	1.69	1.98	0.0665	0.0780
E	3.20	3.40	0.1260	0.1358
E2	2.15	2.59	0.0846	0.1020
e	0.65 BSC		0.0256 BSC	
L	0.30	0.55	0.0118	0.0217
M	0.59	---	0.0232	---
O	10Deg	12Deg	10Deg	12Deg

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: http://www.irf.com/technical-info/appnotes/an-1136.pdf
For more information on package inspection techniques, please refer to application note AN-1154: http://www.irf.com/technical-info/appnotes/an-1154.pdf

PQFN 3.3mm x 3.3mm Outline Part Marking



TOP MARKING (LASER)

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

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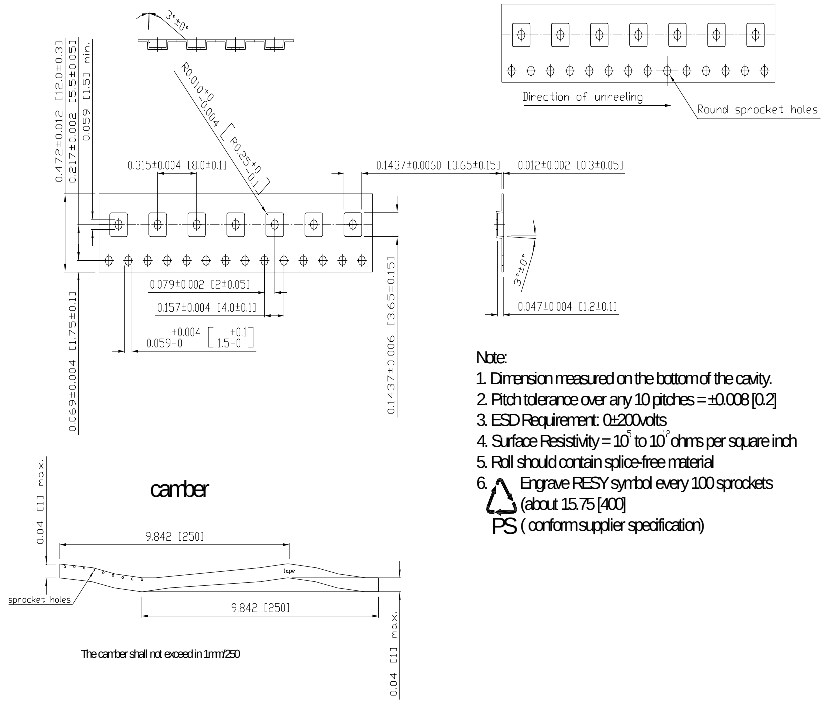
PQFN 3.3mm x 3.3mm Outline Tape and Reel



Qualification Information†

Qualification Level	Consumer†† (per JEDEC JESD47F††† guidelines)	
Moisture Sensitivity Level	PQFN 3.3mm x 3.3mm	MSL1 (per JEDEC J-STD-020D†††)
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/

††† Applicable version of JEDEC standard at the time of product release.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting $T_J = 25°C$, L = 0.29mH, $R_G = 50\Omega$, $I_{AS} = 20A$.

③ Pulse width ≤ 400μs; duty cycle ≤ 2%.

④ R_θ is measured at T_J of approximately 90°C.

⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

⑥ Calculated continuous current based on maximum allowable junction temperature.

⑦ Current is limited to 25A by source bonding technology.

International Rectifier

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To contact International Rectifier, please visit http://www.irf.com/whoto-call/

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